

Hoon Hahn Yoon

List of Publications by Year in descending order

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13
papers

165
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1163117

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times ranked

255
citing authors

#	ARTICLE	IF	CITATIONS
1	Switchable Photoresponse Mechanisms Implemented in Single van der Waals Semiconductor/Metal Heterostructure. ACS Nano, 2022, 16, 568-576.	14.6	29
2	Molybdenum Disulfide/Double-Wall Carbon Nanotube Mixed-Dimensional Heterostructures. Advanced Materials Interfaces, 2022, 9, .	3.7	6
3	On-chip photonics and optoelectronics with a van der Waals material dielectric platform. Nanoscale, 2022, 14, 9459-9465.	5.6	4
4	Inducing Strong Light-Matter Coupling and Optical Anisotropy in Monolayer MoS ₂ with High Refractive Index Nanowire. ACS Applied Materials & Interfaces, 2022, 14, 31140-31147.	8.0	4
5	Graphene/Bi ₂ Se ₃ Heterojunction Phototransistor Using Photogating Effect Modulated by Tunable Tunneling Resistance. , 2021, , .		1
6	Multilayer MoTe ₂ Field-Effect Transistor at High Temperatures. Advanced Materials Interfaces, 2021, 8, 2100950.	3.7	14
7	Tunable Quantum Tunneling through a Graphene/Bi ₂ Se ₃ Heterointerface for the Hybrid Photodetection Mechanism. ACS Applied Materials & Interfaces, 2021, 13, 58927-58935.	8.0	10
8	Multi-Level Capacitive Memory Effect in Metal/Oxide/Floating-Schottky Junction. Journal of the Korean Physical Society, 2019, 74, 979-983.	0.7	1
9	Reduction of water-molecule-induced current-voltage hysteresis in graphene field effect transistor with semi-dry transfer using flexible supporter. Journal of Applied Physics, 2019, 125, .	2.5	12
10	Negative Fermi-Level Pinning Effect of Metal/n-GaAs(001) Junction Induced by a Graphene Interlayer. ACS Applied Materials & Interfaces, 2019, 11, 47182-47189.	8.0	11
11	One-Dimensional Assembly on Two-Dimensions: AuCN Nanowire Epitaxy on Graphene for Hybrid Phototransistors. Nano Letters, 2018, 18, 6214-6221.	9.1	30
12	Strong Fermi-Level Pinning at Metal/n-Si(001) Interface Ensured by Forming an Intact Schottky Contact with a Graphene Insertion Layer. Nano Letters, 2017, 17, 44-49.	9.1	26
13	Schottky barrier modulation of metal/4H-SiC junction with thin interface spacer driven by surface polarization charge on 4H-SiC substrate. Applied Physics Letters, 2015, 107, .	3.3	17